

N-Channel 60 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY

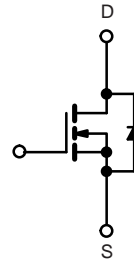
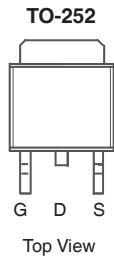
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a
60	0.0023 at V _{GS} = 10 V	120
	0.0049 at V _{GS} = 4.5 V	75

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



RoHS
COMPLIANT



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Gate-Source Voltage	V _{GS}	± 20	V
Continuous Drain Current (T _J = 175 °C) ^b	I _D	T _C = 25 °C	120
		T _C = 100 °C	85 ^a
Pulsed Drain Current	I _{DM}	480	A
Continuous Source Current (Diode Conduction)	I _S	110 ^a	
Avalanche Current	I _{AS}	120	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH E _{AS}	288	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	205
		T _A = 25 °C	5.6 ^b
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 sec	9	15
		Steady State	15	45
Maximum Junction-to-Case	R _{thJC}	0.95	1.5	°C/W

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t ≤ 10 s.

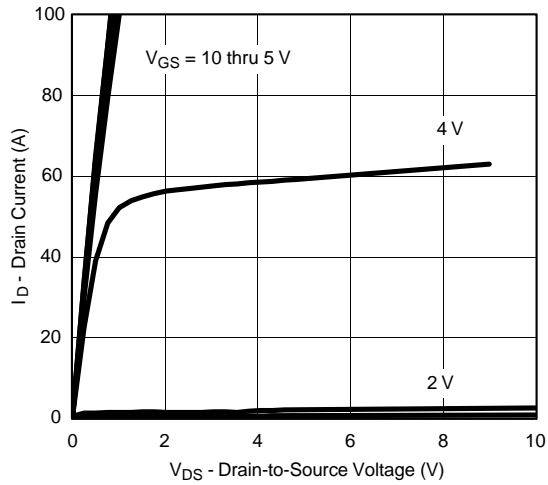
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	-	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	150			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0023	0.0033	Ω
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.0032	0.0040	
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.0039	0.0048	
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.0049	0.0062	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 48\text{ V}, I_D = 20\text{ A}$		165		S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 48\text{ V}, f = 1\text{ MHz}$		10100		μF
Output Capacitance	C_{oss}			1588		
Reverse Transfer Capacitance	C_{rss}			157		
Total Gate Charge ^c	Q_g	$V_{DS} = 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		74	89	nC
Gate-Source Charge ^c	Q_{gs}			15		
Gate-Drain Charge ^c	Q_{gd}			19		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 48\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		18		ns
Rise Time ^c	t_r			32		
Turn-Off Delay Time ^c	$t_{d(off)}$			66		
Fall Time ^c	t_f			13		
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				480	A
Diode Forward Voltage	V_{SD}	$I_F = 20\text{ A}, V_{GS} = 0\text{ V}$			1.25	V
Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		73		ns

Notes:

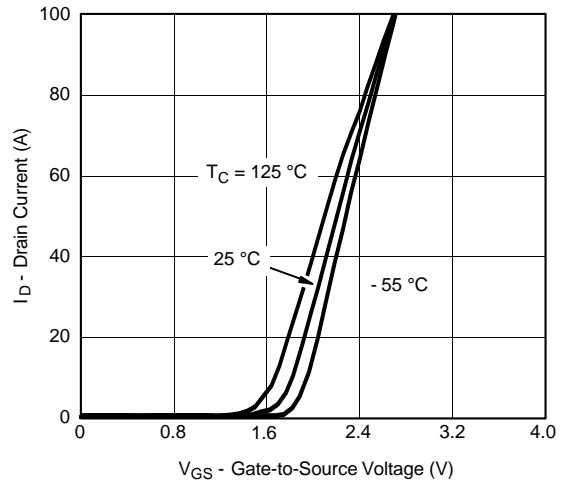
- For design aid only; not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

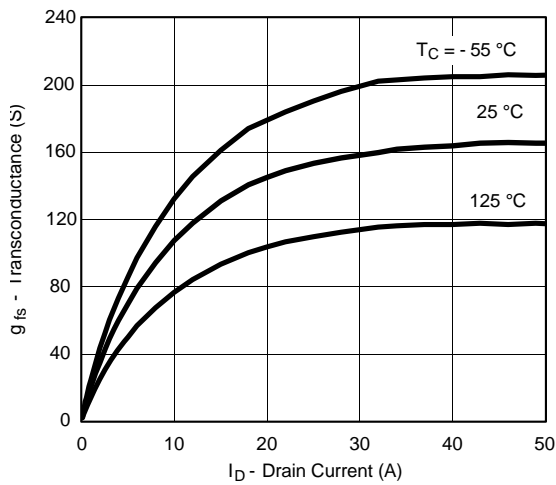
TYPICAL CHARACTERISTICS (25 °C unless noted)



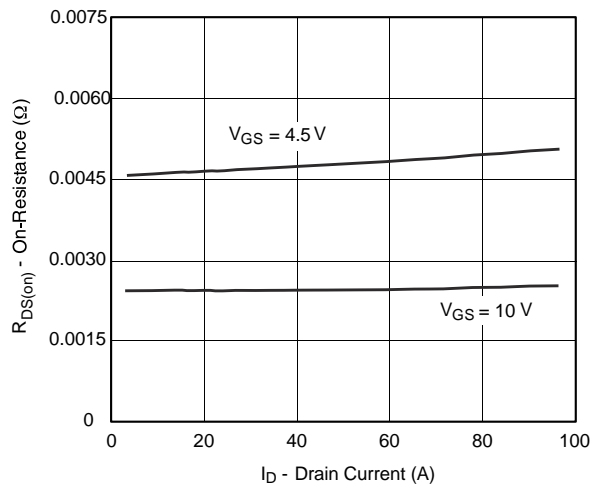
Output Characteristics



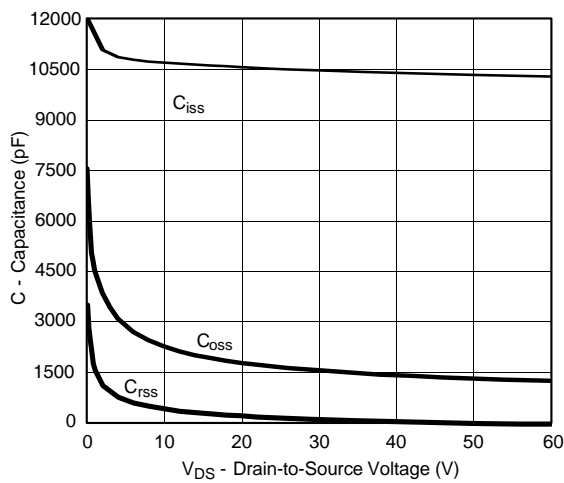
Transfer Characteristics



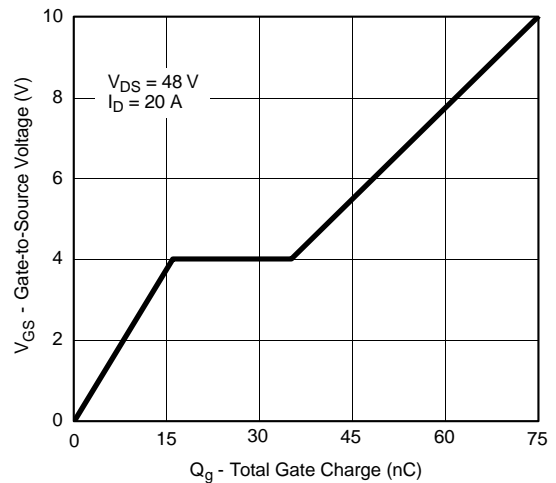
Transconductance



On-Resistance vs. Drain Current

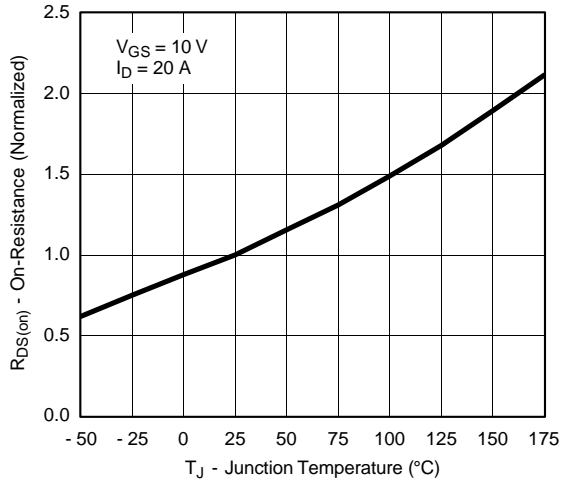


Capacitance

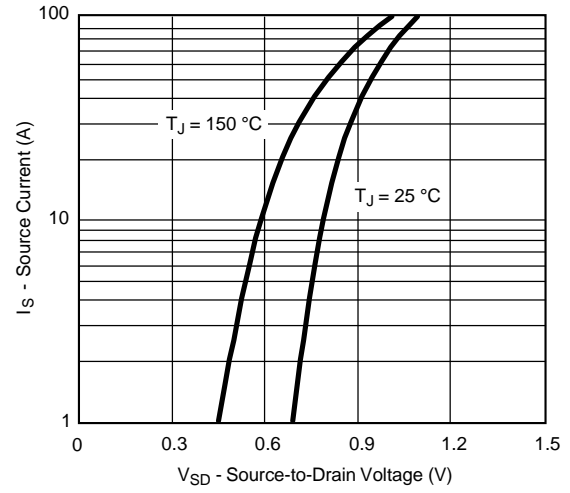


Gate Charge

TYPICAL CHARACTERISTICS (25 °C unless noted)

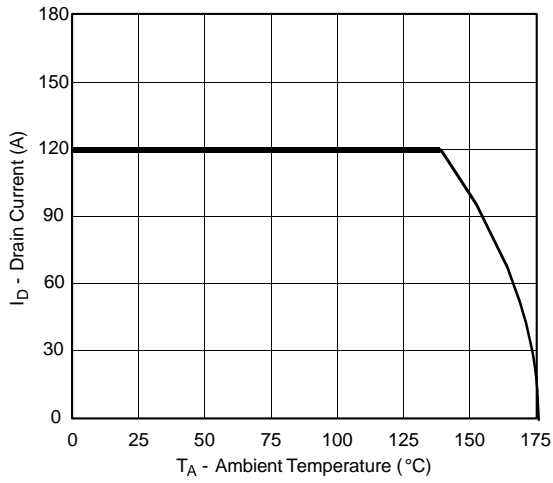


On-Resistance vs. Junction Temperature

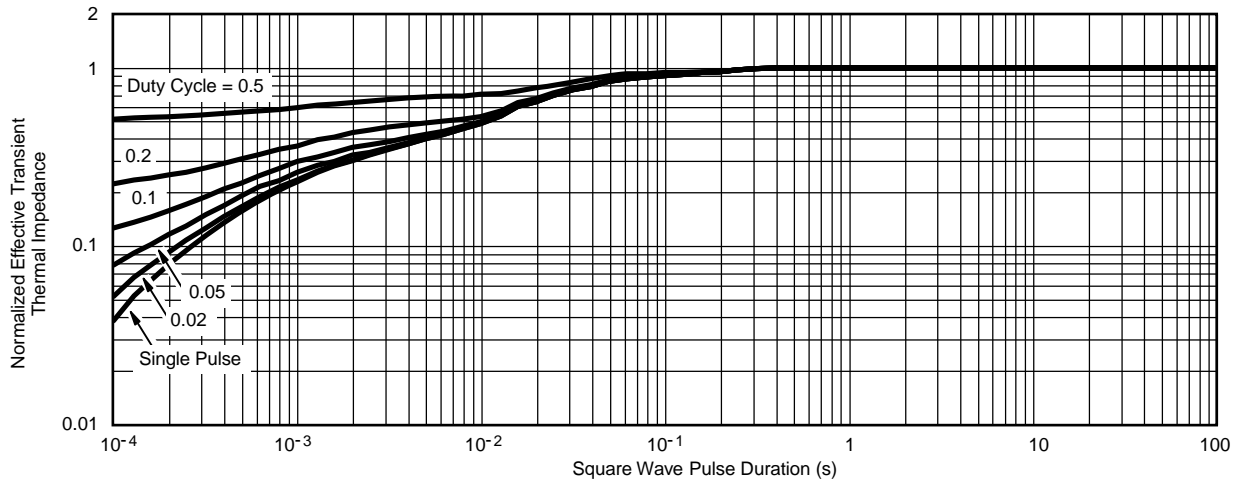
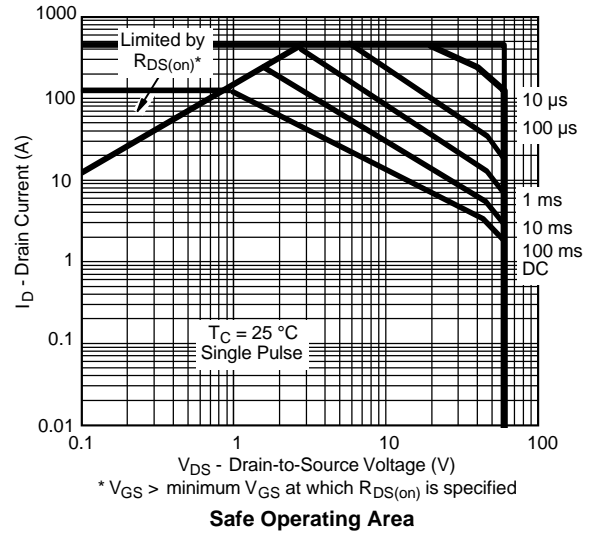


Source-Drain Diode Forward Voltage

THERMAL RATINGS

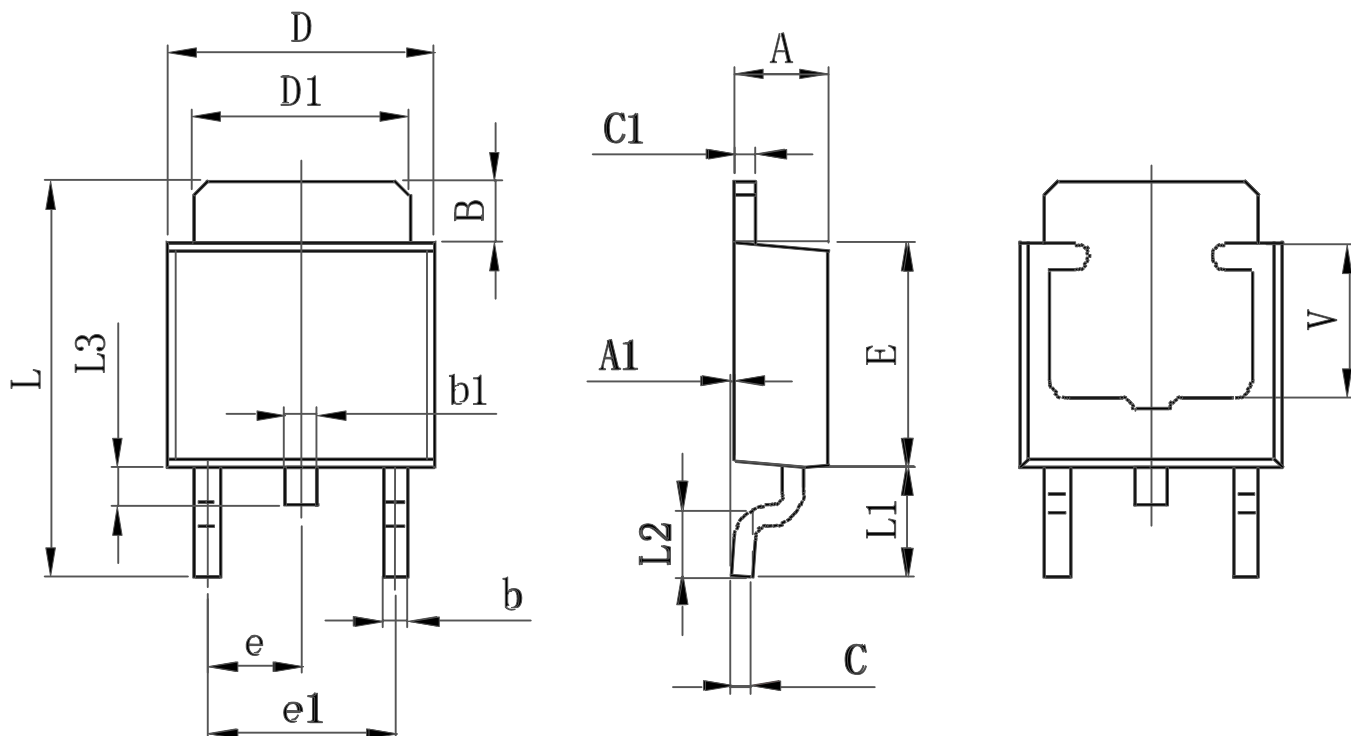


Maximum Drain Current vs. Ambient Temperature



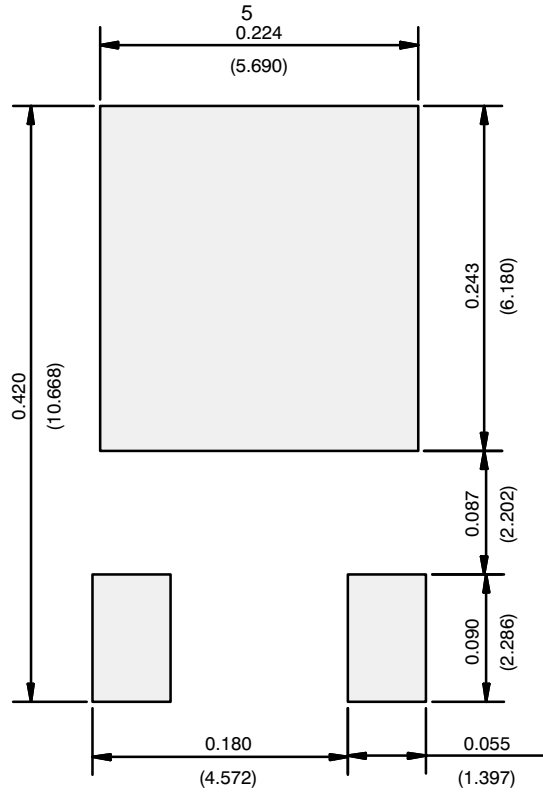
Normalized Thermal Transient Impedance, Junction-to-Case

TO-252-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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